TMS8003 - Low EMI 3.0W Mono Audio Amplifier

FEATURES

- Supply Voltage from 2.5V to 6.0V
- 3.0W@10% THD Output with a 4Ω Load at 5V Supply
- High Efficiency Up to 90% @1W with an 8Ω Speaker
- Shutdown Current <1µA
- Superior Low Noise without Input
- EMI Suppressing by Soft-Driving
- Short Circuit Protection
- Thermal Shutdown
- Available in Space Saving COL-9L Package

APPLICATIONS

- Wearable Device
- Cellphones
- Telephone Watches
- IPCs
- Portable Device
- AIO

GENERAL DESCRIPTION

The TMS8003 is a mono filter-less class-D amplifier with high SNR and differential input that eliminate noise.

Features like higher than 90% efficiency and small PCB areas make the TMS8003 class-D amplifier ideal for portable devices. The filter-less architecture requires no external output filter, fewer external components, less PCB areas and lower system costs, and simplifies application design.

With the soft-driving technology, the edge of the PWM at output stage is very flat which is very useful for EMI suppressing.

The TMS8003 features short circuit protection, thermal shutdown and under voltage lock-out.
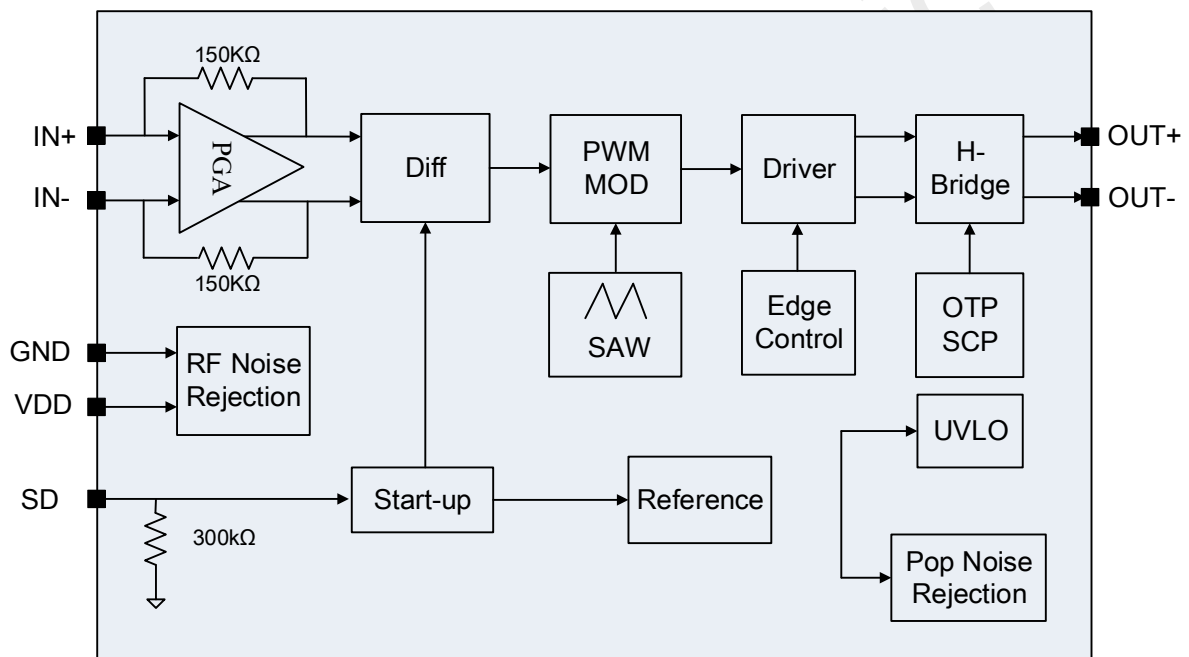
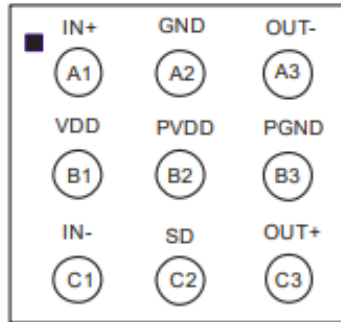The TMS8003 is available in COL-9L packages.

TYPICAL APPLICATION

Differential Input

Single-ended Input
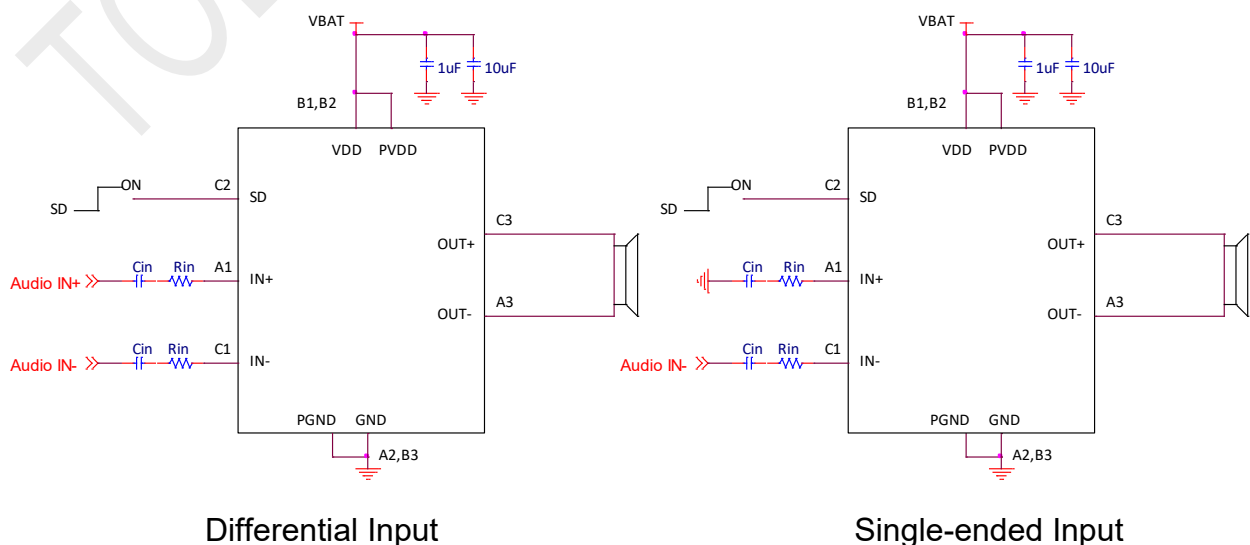
ABSOLUTE MAXIMUM RATINGS

Parameter	Rating	Unit
V_{DD} Supply Voltage	6.5	V
Minimum Output Impedance	3.0	Ω
Input Voltage (IN+, IN-, SD)	-0.3 to V_{DD}+0.3	V
Storage Temperature	-65 to 150	°C
Maximum Junction Temperature	150	°C

Block Diagram

PIN CONFIGURATION

COL1.5x1.5-9L (Top View)

PIN FUNCTIONS

Pin Number	Pin name	Description
A1	IN+	Positive Differential Input
A2	GND	Ground
A3	OUT-	Negative BTL Output
B1	V_{DD}	Power Supply
B2	PV_{DD}	Power Supply
B3	PGND	Power Ground
C1	IN-	Negative Differential Input
C2	SD	Shutdown Control
C3	OUT+	Positive BTL Output

Ordering Information & Marking

Part Number	Package	Marking	Quantity/ Reel
TMS8003AK-TR	COL1.5x1.5-9L	AK YW	3000

TMS8003 devices are Pb-free and RoHS compliant.

ESD RATING

Items	Description	Value	Unit
V_{ESD_HBM}	Human Body Model	±4000	V
V_{ESD_CDM}	Charge Device Model	±750	V

JEDEC specification JS-001

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{DD}	Supply Voltage	2.5	6.0	V
T_a	Operating Ambient Temperature Range	-25	85	℃
T_J	Junction Temperature Range	-40	125	℃

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ELECTRICAL CHARACTERISTICS

(T$_a$=25°C, V$_{DD}$=5V, R$_{IN}$=20KΩ, C$_{IN}$=0.22uF, R$_L$=L(33μH) + R+L(33μH), unless otherwise noted.)

Symbol	Parameter	Test Conditions		MIN	TYP	MAX	UNIT
Po	Output Power	THD+N=10%, f=1kHz, R$_L$=4Ω	V$_{DD}$=5.0V		3.0		W
			V$_{DD}$=3.7V		1.65		
		THD+N=1%, f=1kHz, R$_L$ =4Ω	V$_{DD}$=5.0V		2.55		W
			V$_{DD}$=3.7V		1.36		
		THD+N=10%, f=1kHz, R$_L$ =8Ω	V$_{DD}$=5.0V		1.72		W
			V$_{DD}$=3.7V		0.94		
		THD+N=1%, f=1kHz, R$_L$ =8Ω	V$_{DD}$=5.0V		1.40		W
			V$_{DD}$=3.7V		0.75		
THD+N	Total Harmonic Distortion Plus Noise	V$_{DD}$=5.0V, Po=0.25W	f=1kHz, R$_L$=8Ω		0.036		%
		V$_{DD}$=3.7V, Po=0.25W			0.015		
		V$_{DD}$=5.0V, Po=0.5W	f=1kHz, R$_L$=4Ω		0.02		%
		V$_{DD}$=3.7V, Po=0.5W			0.026		
PSRR	Power Supply Ripple Rejection	V$_{DD}$=5V, Inputs AC-Grounded,	f=217Hz		-75		dB
			f=1kHz		-75		
SNR	Signal-to-Noise Ratio	THD=1%, f=1kHz	A-weighting		96		dB
Vn	Output Noise	Inputs AC-Grounded, G$_V$=6dB	No A-weighting		55		μV
			A-weighting		51		
G$_V$	Closed-loop Gain	V$_{DD}$= 5V			300K/Rin		V/V
fsw	Switching Frequency	V$_{DD}$= 5V			590		kHz
η	Efficiency	R$_L$=8Ω, THD=10%	f=1kHz		91		%
		R$_L$=4Ω, THD=10%			87		
I$_Q$	Quiescent Current	V$_{DD}$=5V	No Load		2.2		mA
		V$_{DD}$=3.7V			1.7		
DC Parameters							
I$_{SD}$	Shutdown Current	V$_{DD}$=5V	CTRL=0V			1	μA
R$_{SDON}$	Static Drain-to Source On-state Resistor	High Side + Low Side	V$_{DD}$=5.0V, I=500mA		400		mΩ
T$_{ON}$	Turn On Time	V$_{DD}$= 5V	C$_{BYP}$=0.1uF		32		ms
V$_{OS}$	Output Offset Voltage	V$_{DD}$=5V	AC-Ground		3.5		mV
VIH	Input High Voltage	V$_{DD}$=5V		1.4			V
VIL	Input Low Voltage	V$_{DD}$=5V				1.0	

PERFORMANCE CHARACTERISTICS

(T_a=25°C, V_{DD}=5V, R_{IN}=20KΩ, C_{IN}=0.22uF, R_L=L(33μH) + R+L(33μH), Differential Input, unless otherwise noted.)
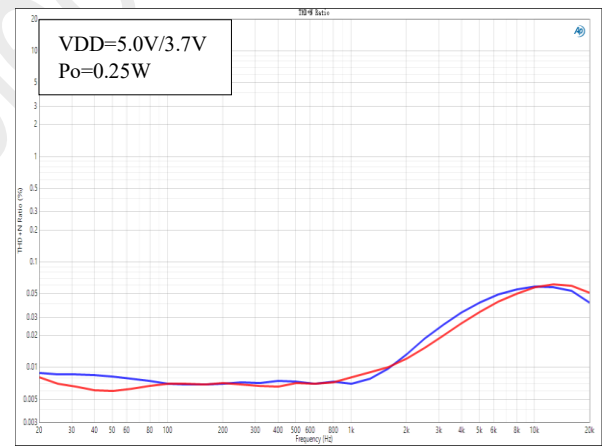
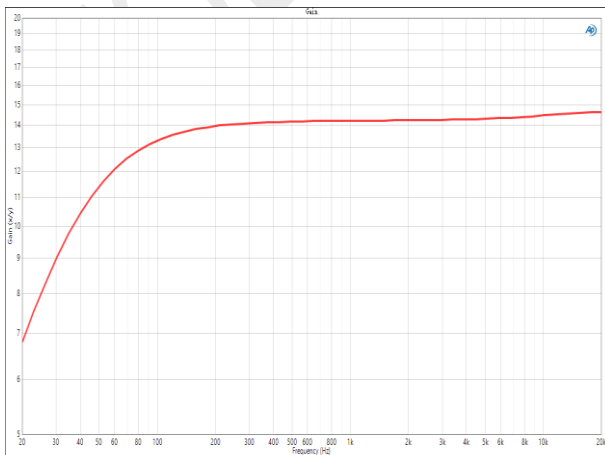THD+N Vs. Output Power (R$_L$=4Ω)
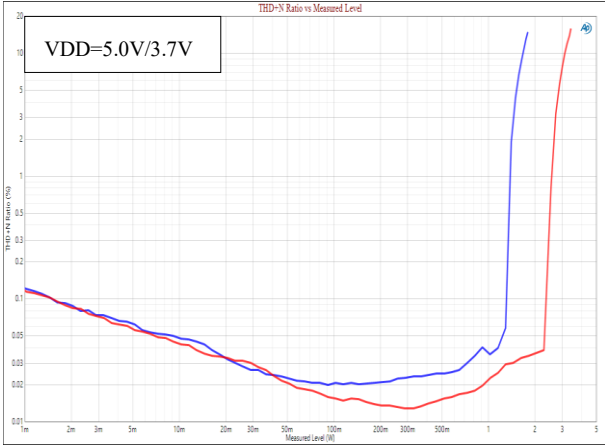
THD+N Vs. Output Power (R$_L$=8Ω)
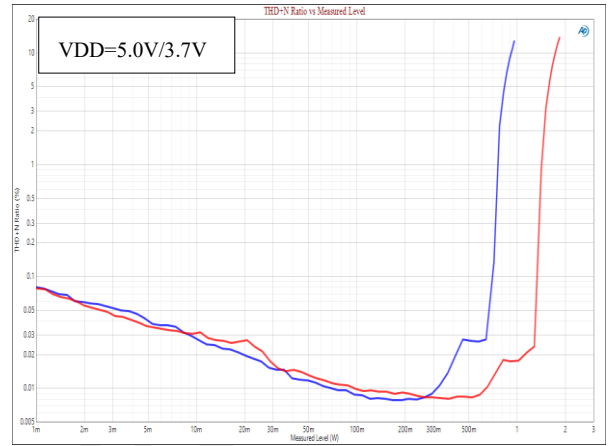
THD+N Vs. Frequency (R$_L$=4Ω)
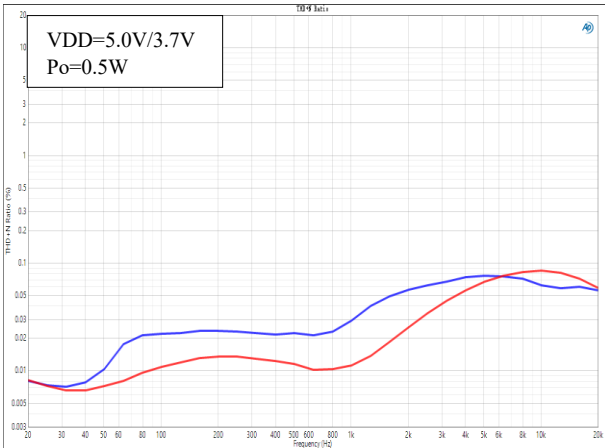
THD+N Vs. Frequency (R$_L$=8Ω)

Frequency Response

Noise Floor
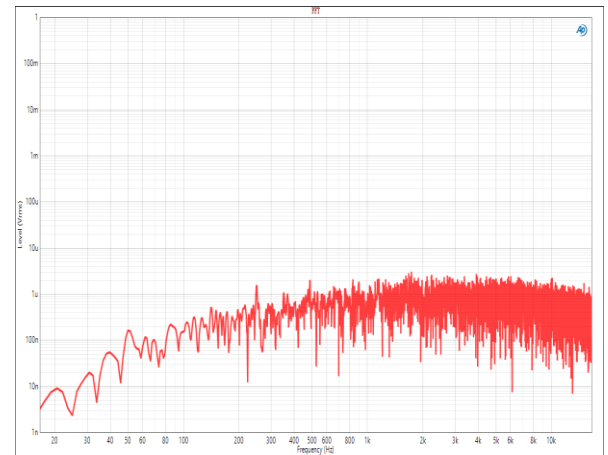
TMS8003

PERFORMANCE CHARACTERISTICS

(T_a=25°C, V_{DD}=5V, R_{IN}=20KΩ, C_{IN}=0.22uF, R_L=L(33μH) + R+L(33μH), unless otherwise noted.)
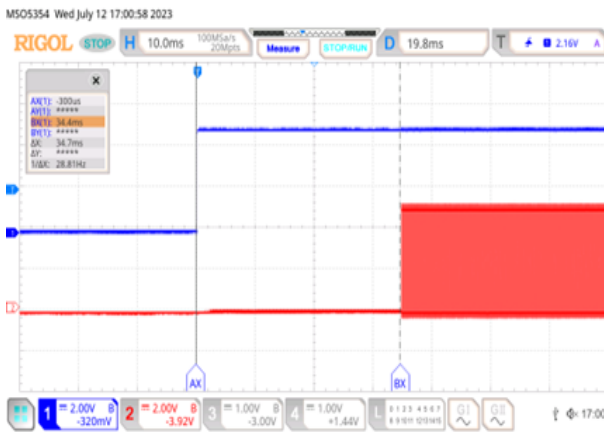
CMRR
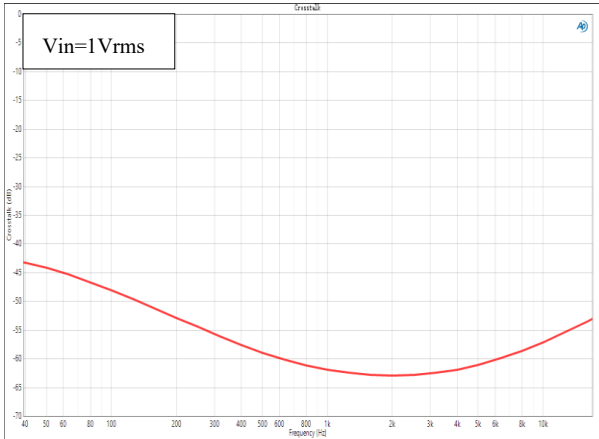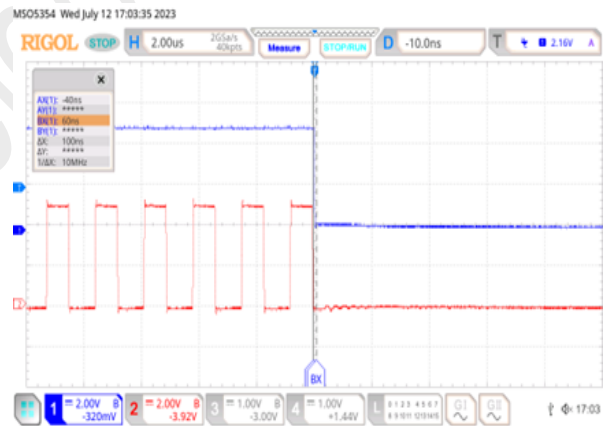

PSRR
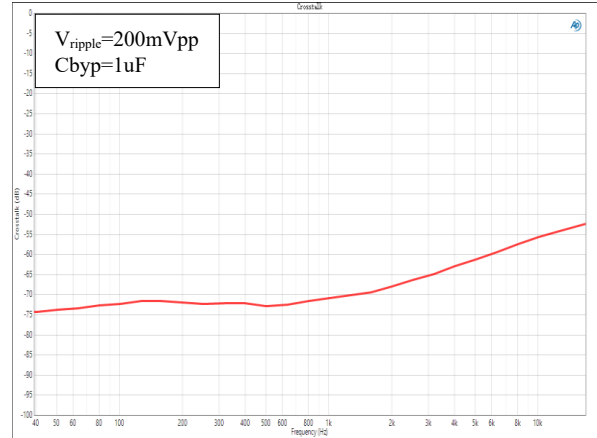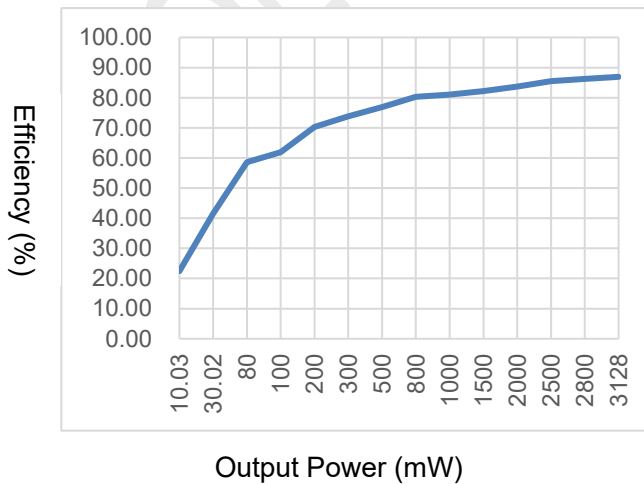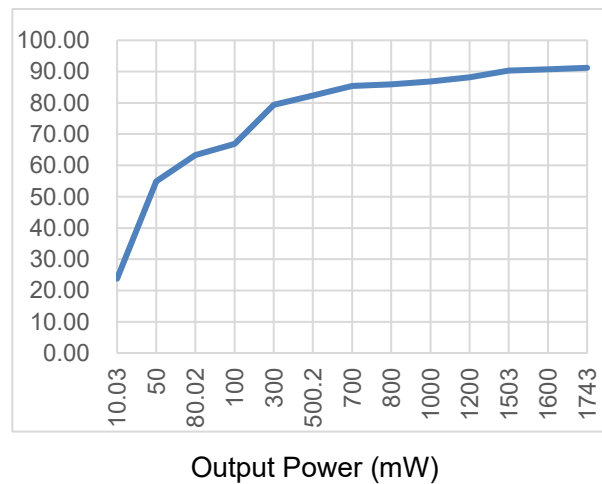

Start-up Response

Shutdown Response

Efficiency Vs. Output Power (R_L=4Ω)

Efficiency Vs. Output Power (R_L=8Ω)

APPLICATION INFORMATION

Input Capacitors (Ci)

In the typical application, an input capacitor, Ci, is required to allow the amplifier to bias the input signal to the proper DC level for optimum operation. In this case, Ci and the minimum input impedance Ri form is a high-pass filter with the corner frequency determined in the follow equation:

$$f_c = \frac{1}{(2\pi R_i C_i)}$$

It is important to consider the value of Ci as it directly affects the low frequency performance of the circuit. For example, when Ri is 160kΩ and the specification calls for a flat bass response are down to 150Hz. Equation is reconfigured as followed:

$$C_i = \frac{1}{(2\pi R_i f_c)}$$

When input resistance variation is considered, the Ci is 7nF, so one would likely choose a value of 10nF. A further consideration for this capacitor is the leakage path from the input source through the input network (Ci, Ri + Rf) to the load. This leakage current creates a DC offset voltage at the input to the amplifier that reduces useful headroom, especially in high gain applications. For this reason, a low-leakage tantalum or ceramic capacitor is the best choice. When polarized capacitors are used, the positive side of the capacitor should face the amplifier input in most applications as the DC level is held at VDD/2, which is likely higher than the source DC level. Please note that it is important to confirm the capacitor polarity in the application.

Decoupling Capacitor (CS)

The TMS8003 is a high-performance CMOS audio amplifier that requires adequate power supply decoupling to ensure the output total harmonic distortion (THD) as low as possible. Power supply decoupling also prevents the oscillations causing by long lead length between the amplifier and the speaker.

The optimum decoupling is achieved by using two different types of capacitors that target on different types of noise on the power supply leads. For higher frequency transients, spikes, or digital hash on the line, a good low Equivalent-Series-Resistance (ESR) ceramic capacitor, typically 1μF, is placed as close as possible to the device VDD pin for the best operation. For filtering lower frequency noise signals, a large ceramic capacitor of 10μF or greater placed near the audio power amplifier is recommended. Long conducting wires on VDD or & and GND (>1m) will cause big power pumping which may damage the chip, that an additional 100uF or greater capacitance placed near the TMS8003 is needed.

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How to Reduce EMI

Most applications require a ferrite bead filter for EMI elimination shown at Figure 1. The ferrite filter reduces EMI around 1MHz and higher. When selecting a ferrite bead, choose one with high impedance at high frequencies, but low impedance at low frequencies.
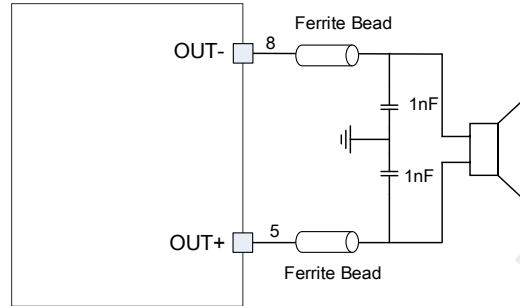
Figure 1. Ferrite Bead Filter to Reduce EMI

APPLICATION INFORMATION

Under Voltage Lock-out (UVLO)

The TMS8003 incorporates circuitry designed to detect low supply voltage. When the supply voltage drops to 2.4V or below, the TMS8003 goes into a state of shutdown, and the device comes out of its shutdown state and restore to normal function only when VDD higher than 2.5V.

Short Circuit Protection (SCP)

The TMS8003 has short circuit protection circuitry on the outputs to prevent the device from damage when output-to-output shorts or output-to-GND shorts occur. When a short circuit occurs, the device immediately goes into shutdown state. Once the short is removed, the device will be reactivated.

Over Temperature Protection (OTP)

Thermal protection on the TMS8003 prevents the device from damage when the internal die temperature exceeds 135°C. There is a 15°C tolerance on this trip point from device to device. Once the die temperature exceeds the set point, the device will enter the shutdown state and the outputs are disabled. This is not a latched fault. The thermal fault is cleared once the temperature of the die decreased by 15°C. This large hysteresis will prevent motor boating sound well and the device begins normal operation at this point with no external system interaction.

Shutdown Operation

In order to reduce power consumption while not in use, the TMS8003 contains shutdown circuitry amplifier off when logic low is placed on the CTRL pin. By switching the CTRL pin connected to GND, the TMS8003 supply current draw will be minimized in idle mode.

POP and Click Circuitry

The TMS8003 contains circuitry to minimize turn-on and turn-off transients or "click and pops", where turn-on refers to either power supply turn-on or device recover from shutdown mode. When the device is turned on, the amplifiers are internally muted. An internal current source ramps up the internal reference voltage. The device will remain in mute mode until the reference voltage reach half supply voltage, 1/2 VDD. As soon as the reference voltage is stable, the device will begin full operation. For the best power-off pop performance, the amplifier should be set in shutdown mode prior to removing the power supply voltage.

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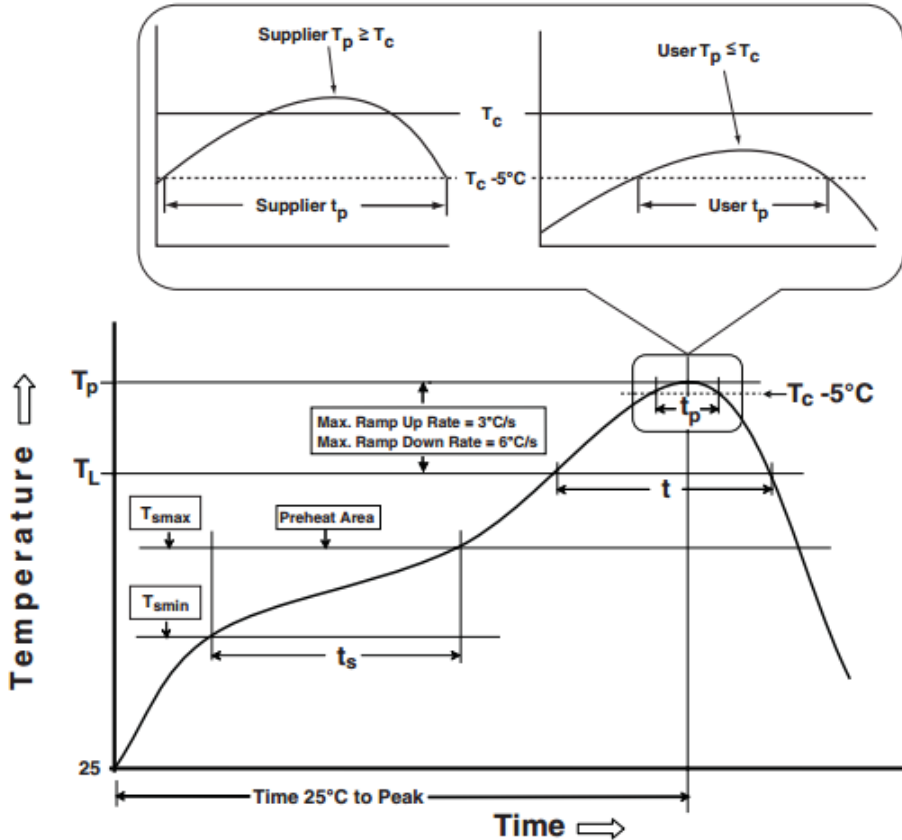TOLL Microelectronic

PACKAGE INFORMATION

COL1.5x1.5-9L

Top View

Bottom View

Side View
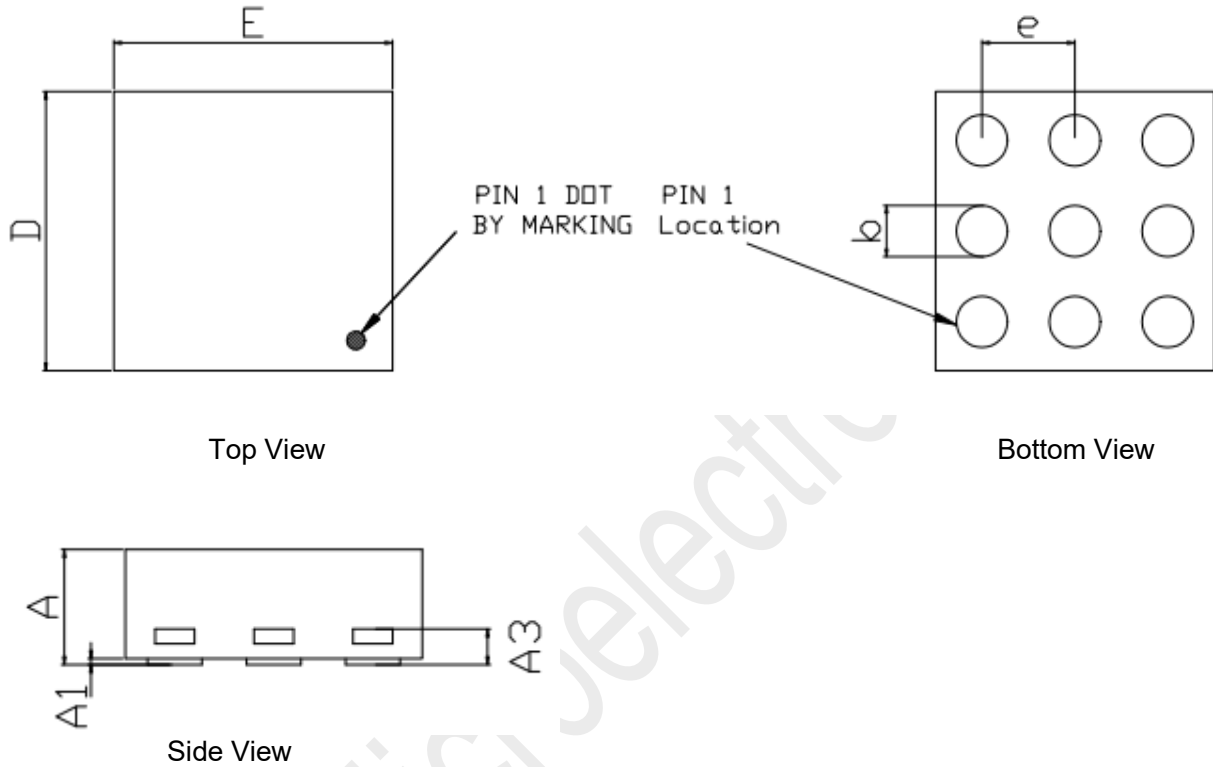
Comom Dimensions (mm)			
PKG.	COL1.5x1.5-9L		
REF.	MIN.	NOM.	MAX.
A	>0.5	0.55	0.60
A1	0.00	-	0.05
A3	0.15 REF.		
D	1.45	1.50	1.55
E	1.45	1.50	1.55
b	D0.250	D0.275	D0.300
e	0.50 BSC		

拓尔产品回流焊温度曲线推荐

我司产品如无特殊说明，回流焊时温度曲线推荐如下：

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat/Soak Temperature Min (T_{smin}) Temperature Max (T_{smax}) Time (t_s) from (T_{smin} to T_{smax})	100 °C 150 °C 60-120 seconds	150 °C 200 °C 60-120 seconds
Ramp-up rate (T_L to T_p)	3 °C/second max.	3 °C/second max.
Liquidous temperature (T_L) Time (t_L) maintained above T_L	183 °C 60-150 seconds	217 °C 60-150 seconds
Peak package body temperature (T_p)	235 °C	260 °C
Time (t_p)* within 5 °C of the specified classification temperature (T_c)	20* seconds	30* seconds
Ramp-down rate (T_p to T_L)	6 °C/second max.	6 °C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile temperature (T_p) is defined as a supplier minimum and a user maximum.		

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